

Appln. No.09/648,191
Amdt dated July 10, 2003
Reply to Office action of April 24, 2003

Amendments to the Specification:

Please add the following header and paragraph at page 1, after the title:

--CROSS-REFERENCE TO RELATED APPLICATIONS

A¹ This Application claims priority to and the benefit of Korean Patent Application No. 1999-35034 filed on August 23, 1999, Korean Patent Application No. 1999-44602 filed on October 14, 1999, and Korean Patent Application No. 2000-80 filed on January 3, 2000.--

Please replace the paragraph beginning at page 7, line 12, with the following rewritten paragraph:

A² --As shown in Fig. 2, the frame 21 has a size corresponding that of the backplate 3, and internally has a plurality of opening portions 21a. The opening portions 21a of the frame 21 are formed such that they correspond to the pixels of the phosphors 11 [9] and the emitters 15. The frame 21 further has spacers 23 for maintaining the cell gap in a constant manner.--

Please replace the paragraph beginning at page 8, line 18, with the following rewritten paragraph:

A³ --As shown in Fig. 10, the gate electrodes 19 are formed on the frame 21 with a predetermined thickness and a stripe pattern. The gate electrodes 19 have opening portions 19a corresponding to the opening portions 21a [21] of the frame 21. The gate electrodes 19 are preferably formed through vapor deposition based on aluminum (Al) or indium tin oxide (ITO).--

Please replace the paragraph beginning at page 11, line 22, with the following rewritten paragraph:

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Q4 --A plurality of cathode electrodes 46 are formed on the backplate 44 with a stripe pattern, and carbon nano-tubes 48 are separately formed on the cathode electrodes 46 as field [filed] emitters while being spaced apart from each other with a predetermined distance.--
